### AMD530C

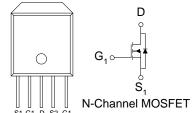
## **Analog Power**

# P & N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(\text{on})}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low  $r_{DS(\text{on})}$  provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	I <sub>D</sub> (A)	
30	$45 @ V_{GS} = 2.5V$	29	
50	$35 @ V_{GS} = 4.5V$	36	
-26.5	$70 @ V_{GS} = -2.5V$	-20	
-20.5	$52 @ V_{GS} = -4.5V$	-26	





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	N-Channel	P-Channel	Units	
Drain-Source Voltage		V <sub>DS</sub>	30	-26.5	V	
Gate-Source Voltage		V <sub>GS</sub>	±12	±12		
Carting on Drain Connect <sup>a</sup>	T <sub>A</sub> =25°C	T	36	-26		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C	ID	30	-21	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	40	-40		
Continuous Source Current (Diode Conduction) <sup>a</sup>		Is	30	-30	А	
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$	P <sub>D</sub>	50	50	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 te	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	50	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	°C/W		

Notes

Surface Mounted on 1" x 1" FR4 Board. a.

Pulse width limited by maximum junction temperature b.

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SPECIFICATIONS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Limits Ch   Min   Typ   Max				Unit	
	Symbol	i est conditions	Ch	Min	Тур	Max	Um	
Static						T		
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{GS} = V_{DS}, I_D = 250 \text{ uA}$	N	0.6			V	
	05(11)	$V_{GS} = V_{DS}$ , $I_D = -250 \text{ uA}$	P P	-0.6		+100		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{GS} = -12 V, V_{DS} = 0 V$ $V_{GS} = 12 V, V_{DS} = 0 V$	P N			$\pm 100 \\ \pm 100$	nA	
Zero Gate Voltage Drain Current	т	$V_{\rm DS} = -24 \text{ V}, V_{\rm DS} = 0 \text{ V}$	P			-1		
	I <sub>DSS</sub>	$V_{DS} = 24 V, V_{GS} = 0 V$	Ν			1	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 4.5 V$	N	20			А	
on State Dian Cartent	-D(on)	$V_{DS} = -5 V, V_{GS} = -4.5 V$	Р	-20		35	А	
		VGS = 4.5 V, ID = 6.9 A VGS = 2.5 V, ID = 6 A	Ν			45	ļ	
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	VGS = 2.5 V, ID = 6 A VGS = -4.5 V, ID = -5.2 A				52	mΩ	
		$VGS = -2.5 V, I_D = -4.2 A$	Р			70		
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 6.9 \text{ A}$ $V_{DS} = -15 \text{ V}, \text{ I}_{D} = -5.2 \text{ A}$	N		25		S	
	Bts	$V_{\rm DS} = -15$ V, $I_{\rm D} = -5.2$ A	Р		10		5	
Dynamic								
Total Gate Charge	Qg	N-Channel	N		6.0			
Total Gate Charge	Qg		Р		25			
Gate-Source Charge	Qgs	$V_{DS} = 15V, V_{GS} = 4.5V, I_{D} = 6.9A$	N P		1.0		nC	
Gate-Drain Charge	<b>1</b> 0°	P-Channel	r N		1.5		ne	
	Qgd	$V_{DS}$ =-15V, $V_{GS}$ =-4.5V, $I_{D}$ =-5.2A	Р		3.9			
	_		r N		7.4			
Turn-On Delay Time	td(on)	N-Chaneel	P		7.6			
		$t_r \qquad \begin{array}{c} V_{\rm DD} = 15V, \ V_{GS} = 4.5V, \ I_D = 1A \ , \\ R_{\rm GEN} = 6\Omega, \end{array}$	N		4		nS	
Rise Time	tr		Р		6.8			
Turn-Off Delay Time	td(off)	P-Channel	N		22.2		ns	
		V <sub>DD</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1A	Р		33.6			
Fall-Time	tf	$R_{GEN}=6\Omega$	N		3.6			
I dil- I line	t1		Р		23.2			

#### Notes

a. Pulse test:  $PW \le 300$  us duty cycle  $\le 2\%$ .

b. Guaranteed by design, not subject to production testing.

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